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BLC10G20LS-240PWT

Power LDMOS transistor

AMPLEON

Rev. 1 — 20 April 2017

Product data sheet

1. Product profile

1.1 General description

240 W LDMOS power transistor with enhanced video bandwidth for base station applications at frequencies from 1805 MHz to 1995 MHz.

Table 1. Typical performance

Typical RF performance at T_{case} = 25 °C in a common source class-AB production test circuit.

Test signal	f	I_{Dq}	V _{DS}	P _{L(AV)}	Gp	η_D	RL_{in}	ACPR _{5M}
	(MHz)	(mA)	(V)	(W)	(dB)	(%)	(dB)	(dBc)
2-carrier W-CDMA	1805 to 1880	1600	28	60	19.3	30	-16	-32 [1]

^[1] Test signal: 3GPP test model 1; 64 DPCH; PAR = 8.4 dB at 0.01 % probability on CCDF per carrier; 5 MHz carrier spacing.

1.2 Features and benefits

- Excellent ruggedness
- Excellent video bandwidth enabling full band operation
- High efficiency
- Low thermal resistance providing excellent thermal stability
- Designed for low memory effects providing excellent pre-distortability
- Device can operate with the supply current delivered through the video leads
- Internally matched for ease of use
- Integrated ESD protection
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

RF power amplifiers for base stations and multi carrier applications in the 1805 MHz to 1995 MHz frequency range

2. Pinning information

Table 2. Pinning

Pin	Description		Simplified ou	utline	Graphic symbol
1	drain1				
2	drain2			2 6	1, 5
3	gate1				3_
4	gate2			7	7
5	video decoupling	[1]		-	* -
6	video decoupling	[1]	3 4	4	2, 6
7	source	[2]			aaa-007731

- [1] Device can operate with the supply current delivered through the combined video decoupling leads.
- [2] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Packag	ackage				
	Name	Description	Version			
BLC10G20LS-240PWT	-	air cavity plastic earless flanged package; 6 leads	SOT1275-1			

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		-6	+13	V
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature	[1]	-	225	°C

^[1] Continuous use at maximum temperature will affect the reliability, for details refer to the online MTF calculator

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-c)}	thermal resistance from junction to case	$T_{case} = 80 ^{\circ}C; P_{L} = 60 W$	0.34	K/W

6. Characteristics

Table 6. DC characteristics

 T_i = 25 °C per section, unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{(BR)DSS}	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 1.49 \text{ mA}$	65	-	-	V
V _{GS(th)}	gate-source threshold voltage	V _{DS} = 10 V; I _D = 149 mA	1.5	2.5	-	V
V_{GSq}	gate-source quiescent voltage	$V_{DS} = 28 \text{ V}; I_D = 800 \text{ mA}$	1.7	2.2	2.7	V
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 32 V	-	-	1.4	μΑ
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 2.37 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	27	-	Α
I _{GSS}	gate leakage current	V _{GS} = 9 V; V _{DS} = 0 V	-	-	140	nA
g _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 7.45 A	-	16	-	S
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 2.37 \text{ V};$ $I_D = 5.2 \text{ A}$	-	0.1	-	Ω

Table 7. RF characteristics

Test signal: 2-carrier W-CDMA; 3GPP test model 1 with 64 DPCH; PAR = 8.4 dB at 0.01 % probability on the CCDF; f_1 = 1807.5 MHz; f_2 = 1812.5 MHz; f_3 = 1872.5 MHz; f_4 = 1877.5 MHz; RF performance at V_{DS} = 28 V; I_{Dq} = 1600 mA; T_{case} = 25 °C; unless otherwise specified; in a water cooled class-AB test circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	P _{L(AV)} = 60 W	18.3	19.3	-	dB
η_{D}	drain efficiency	P _{L(AV)} = 60 W	26.5	30	-	%
RLin	input return loss	P _{L(AV)} = 60 W	-	-16	-11	dB
ACPR _{5M}	adjacent channel power ratio (5 MHz)	P _{L(AV)} = 60 W	-	-32	-28	dBc

7. Test information

7.1 Ruggedness in class-AB operation

The BLC10G20LS-240PWT is capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: V_{DS} = 28 V; I_{Dq} = 1600 mA; 2-carrier W-CDMA signal; P_L = 120 W average; f_c = 1805 MHz; 5 MHz spacing; 46 % clipping.

7.2 Impedance information

Table 8. Typical impedance

Measured load-pull data per section; I_{Dq} = 800 mA; V_{DS} = 28 V; pulsed CW (t_p = 100 μ s; δ = 10 %).

f	Z _S [1]	Z _L [1]	P _L [2]	η _D [2]	G _p [2]
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)
Maximum	power load			'	
1805	3.0 – j9.0	2.2 – j6.9	213.8	62.3	16.1
1840	3.6 – j9.6	2.2 – j7.1	213.4	61.8	16.2
1880	4.0 – j10.0	2.3 – j7.2	211.9	62.2	16.4
1930	6.4 – j10.5	2.3 – j7.2	208.5	62.3	16.6
1960	7.0 – j11.0	2.1 – j7.1	206.6	60.3	16.5
1990	9.0 – j10.3	2.3 – j7.2	203.8	62.2	16.9
Maximum	drain efficiency loa	nd	,	'	,
1805	3.0 - j9.0	4.6 – j6.8	162.2	70.4	18.1
1840	3.6 – j9.6	4.1 – j6.2	164.7	70.2	18.2
1880	4.0 – j10.0	3.8 – j6.3	161.6	69.9	18.3
1930	6.4 – j10.5	3.6 – j5.9	159.1	69.3	18.4
1960	7.0 – j11.0	3.6 – j5.8	157.1	68.6	18.5
1990	9.0 – j10.3	3.2 – j5.7	154.4	68.3	18.6

- [1] Z_S and Z_L defined in Figure 1.
- [2] at 3 dB gain compression.

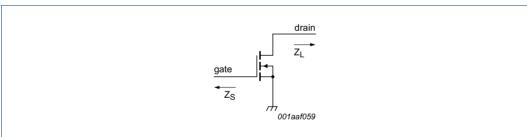


Fig 1. Definition of transistor impedance

7.3 Test circuit

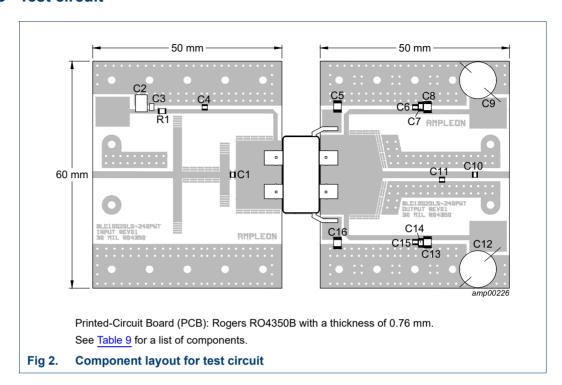
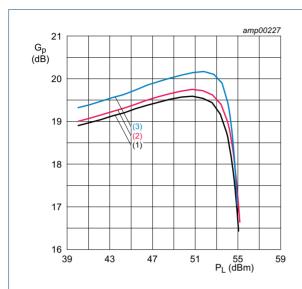


Table 9. List of components See Figure 2 for component layout.

Component	Description	Value	Remarks
C1	multilayer ceramic chip capacitor	1.5 pF	ATC 800A
C2	multilayer ceramic chip capacitor	1 μF	Murata
C3	multilayer ceramic chip capacitor	100 nF	Murata
C4, C6, C10, C15	multilayer ceramic chip capacitor	43 pF	ATC 800A
C5, C8, C13, C16	multilayer ceramic chip capacitor	4.7 μF, 100 V	Murata
C7, C14	multilayer ceramic chip capacitor	220 nF	Murata
C9, C12	electrolytic capacitor	> 470 μF, 63 V	low ESR
C11	multilayer ceramic chip capacitor	1.2 pF	ATC 800A
R1	resistor	4.7 Ω, 1 % tolerance	SMD 0805

7.4 Graphical data

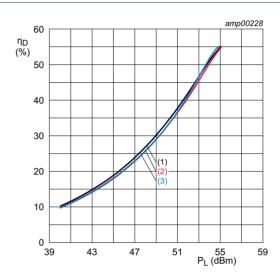
7.4.1 Pulsed CW



 V_{DS} = 28 V; I_{Dq} = 1600 mA; t_p = 100 $\mu s; \, \delta$ = 10 %.

- (1) f = 1805 MHz
- (2) f = 1840 MHz
- (3) f = 1880 MHz

Fig 3. Power gain as a function of output power; typical values

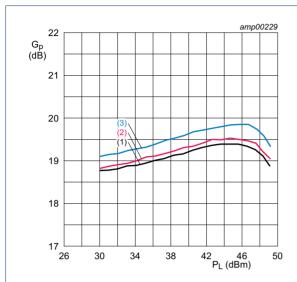


 V_{DS} = 28 V; I_{Dq} = 1600 mA; t_p = 100 μ s; δ = 10 %.

- (1) f = 1805 MHz
- (2) f = 1840 MHz
- (3) f = 1880 MHz

Fig 4. Drain efficiency as a function of output power; typical values

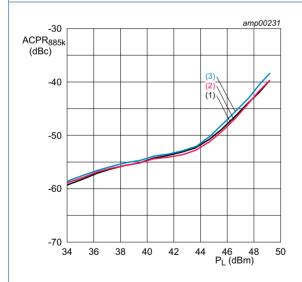
7.4.2 IS-95



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1600 \text{ mA}.$

- (1) f = 1810 MHz
- (2) f = 1840 MHz
- (3) f = 1875 MHz

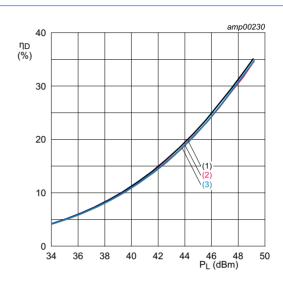
Fig 5. Power gain as a function of output power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1600 \text{ mA}.$

- (1) f = 1810 MHz
- (2) f = 1840 MHz
- (3) f = 1875 MHz

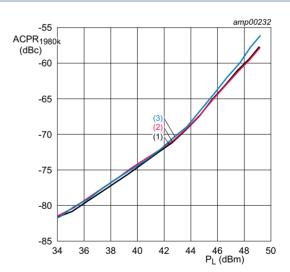
Fig 7. Adjacent channel power ratio (885 kHz) as a function of output power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1600 \text{ mA}.$

- (1) f = 1810 MHz
- (2) f = 1840 MHz
- (3) f = 1875 MHz

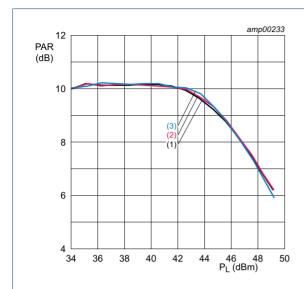
Fig 6. Drain efficiency as a function of output power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1600 \text{ mA}.$

- (1) f = 1810 MHz
- (2) f = 1840 MHz
- (3) f = 1875 MHz

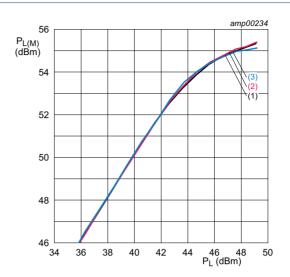
Fig 8. Adjacent channel power ratio (1980 kHz) as a function of output power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1600 \text{ mA}.$

- (1) f = 1810 MHz
- (2) f = 1840 MHz
- (3) f = 1875 MHz

Fig 9. Peak-to-average ratio as a function of output power; typical values

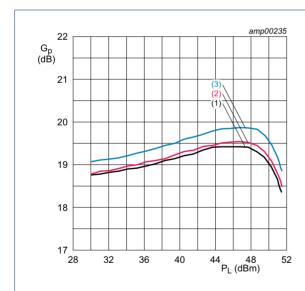


 $V_{DS} = 28 \text{ V}; I_{Dq} = 1600 \text{ mA}.$

- (1) f = 1810 MHz
- (2) f = 1840 MHz
- (3) f = 1875 MHz

Fig 10. Peak output power as a function of output power; typical values

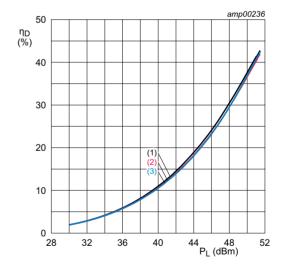
7.4.3 1-Carrier W-CDMA



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1600 \text{ mA}.$

- (1) f = 1807.5 MHz
- (2) f = 1840 MHz
- (3) f = 1877.5 MHz

Fig 11. Power gain as a function of output power; typical values



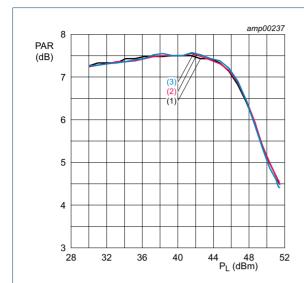
 V_{DS} = 28 V; I_{Dq} = 1600 mA.

- (1) f = 1807.5 MHz
- (2) f = 1840 MHz
- (3) f = 1877.5 MHz

Fig 12. Drain efficiency as a function of output power; typical values

BLC10G20LS-240PWT

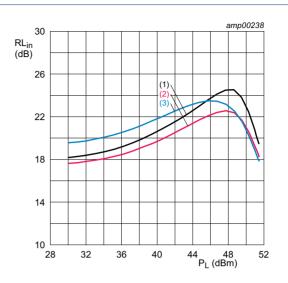
Power LDMOS transistor



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1600 \text{ mA}.$

- (1) f = 1807.5 MHz
- (2) f = 1840 MHz
- (3) f = 1877.5 MHz

Fig 13. Peak-to-average ratio as a function of output power; typical values

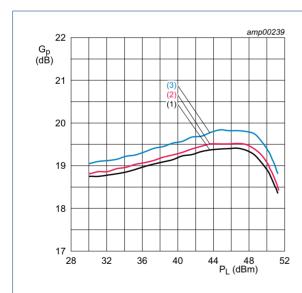


 $V_{DS} = 28 \text{ V}; I_{Dq} = 1600 \text{ mA}.$

- (1) f = 1807.5 MHz
- (2) f = 1840 MHz
- (3) f = 1877.5 MHz

Fig 14. Input return loss as a function of output power; typical values

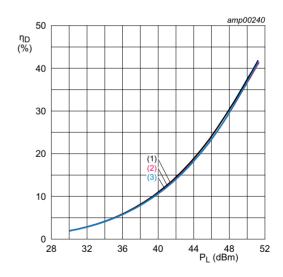
7.4.4 2-Carrier W-CDMA



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1600 \text{ mA}.$

- (1) f = 1810 MHz
- (2) f = 1840 MHz
- (3) f = 1875 MHz

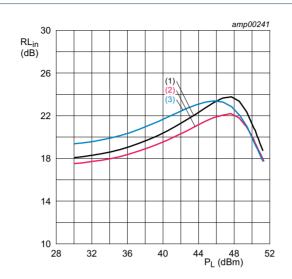
Fig 15. Power gain as a function of output power; typical values



 V_{DS} = 28 V; I_{Dq} = 1600 mA.

- (1) f = 1810 MHz
- (2) f = 1840 MHz
- (3) f = 1875 MHz

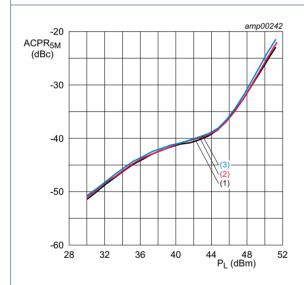
Fig 16. Drain efficiency as a function of output power; typical values



 V_{DS} = 28 V; I_{Dq} = 1600 mA.

- (1) f = 1810 MHz
- (2) f = 1840 MHz
- (3) f = 1875 MHz

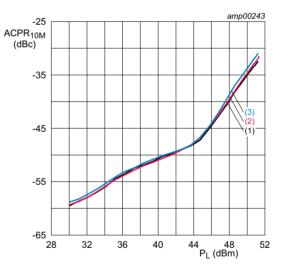
Fig 17. Input return loss as a function of output power; typical values



 V_{DS} = 28 V; I_{Dq} = 1600 mA.

- (1) f = 1810 MHz
- (2) f = 1840 MHz
- (3) f = 1875 MHz

Fig 18. Adjacent channel power ratio (5 MHz) as a function of output power; typical values

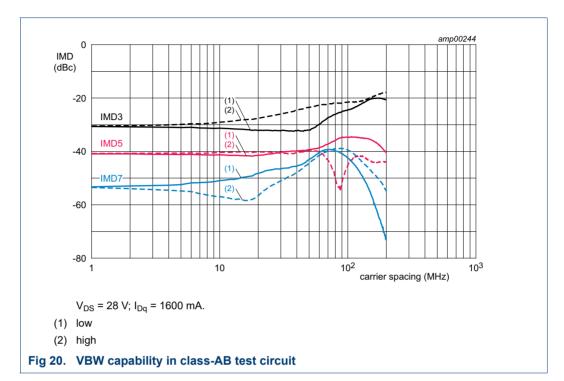


 V_{DS} = 28 V; I_{Dq} = 1600 mA.

- (1) f = 1810 MHz
- (2) f = 1840 MHz
- (3) f = 1875 MHz

Fig 19. Adjacent channel power ratio (10 MHz) as a function of output power; typical values

7.4.5 2-Tone VBW



8. Package outline

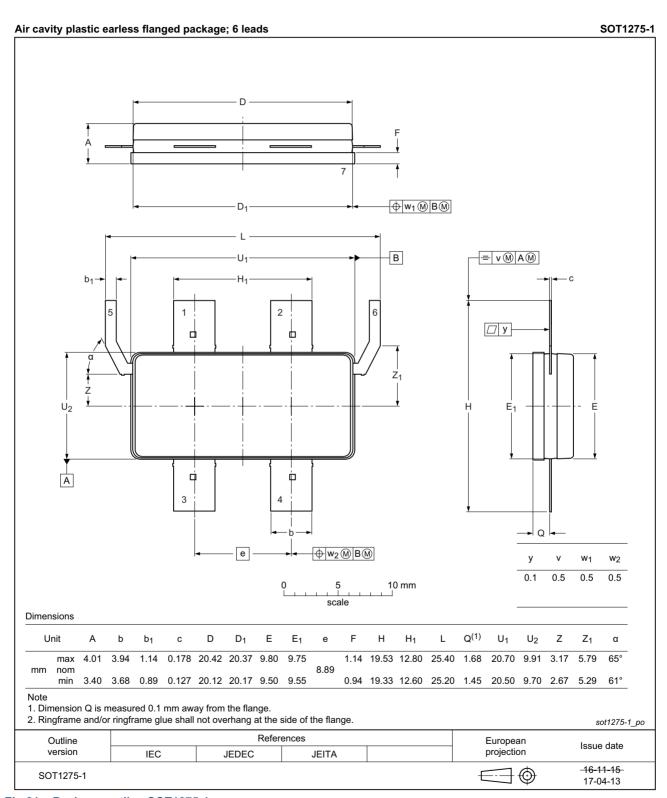


Fig 21. Package outline SOT1275-1

9. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 10. ESD sensitivity

ESD model	Class
Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002	C2A [1]
Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001	2 [2]

^[1] CDM classification C2A is granted to any part that passes after exposure to an ESD pulse of 500 V, but fails after exposure to an ESD pulse of 750 V.

10. Abbreviations

Table 11. Abbreviations

Acronym	Description
3GPP	3rd Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
ESD	ElectroStatic Discharge
LDMOS	Laterally Diffused Metal Oxide Semiconductor
MTF	Median Time to Failure
PAR	Peak-to-Average Ratio
SMD	Surface Mounted Device
VSWR	Voltage Standing Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

11. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLC10G20LS-240PWT v.1	20170420	Product data sheet	-	-

^[2] HBM classification 2 is granted to any part that passes after exposure to an ESD pulse of 2000 V, but fails after exposure to an ESD pulse of 4000 V.

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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Power LDMOS transistor

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13. Contact information

For more information, please visit: http://www.ampleon.com

For sales office addresses, please visit: http://www.ampleon.com/sales

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Power LDMOS transistor

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